



FDBL0150N60 Information

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Part Number FDBL0150N60

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 300A

Package 8-PowerSFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FDBL0150N60 Specifications

Manufacturer Part Number Manufacturer Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-PowerSFN Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Rds On (Max) @ Id, Vgs 1.5 mOhm @ 80A, 10V		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackage8-PowerSFNSeriesPowerTrench?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C240A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs169nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10300pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)357W (Tj)Rds On (Max) @ Id, Vgs1.5 mOhm @ 80A, 10V	Manufacturer Part Number	FDBL0150N60
Package 8-PowerSFN Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 240A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 169nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10300pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 357W (Tj) Rds On (Max) @ Id, Vgs 1.5 mOhm @ 80A, 10V	Manufacturer	Fairchild/ON Semiconductor
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Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 240A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 169nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10300pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 357W (Tj) Rds On (Max) @ Id, Vgs 1.5 mOhm @ 80A, 10V		Transistors - FETs, MOSFETs - Single
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Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 240A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 169nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10300pF @ 30V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5 mOhm @ 80A, 10V	FET Type	N-Channel
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Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 169nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10300pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 357W (Tj) Rds On (Max) @ Id, Vgs 1.5 mOhm @ 80A, 10V	Current - Continuous Drain (Id) @ 25°C	240A (Tc)
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Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 357W (Tj) Rds On (Max) @ Id, Vgs 1.5 mOhm @ 80A, 10V	Gate Charge (Qg) (Max) @ Vgs	169nC @ 10V
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Rds On (Max) @ Id, Vgs 1.5 mOhm @ 80A, 10V	FET Feature	-
	Power Dissipation (Max)	357W (Tj)
Operating Townsenture	Rds On (Max) @ Id, Vgs	1.5 mOhm @ 80A, 10V
Operating Temperature -55°C ~ 1/5°C (1J)	Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package 8-PSOF	Supplier Device Package	8-PSOF
Package / Case 8-PowerSFN	Package / Case	8-PowerSFN
Report errors?		Report errors?

FDBL0150N60 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FDBL0150N60 Payment Methods





















FDBL0150N60 Shipping Methods













If you have any question about FDBL0150N60, please do not hesitate to contact us!

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